N-Channel 120-V (D-S) MOSFET

Key Features:

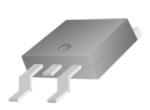
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

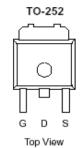
Typical Applications:

- · LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
120	10 @ V _{GS} = 10V	52	
	14 @ $V_{GS} = 6.5V$	44	







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			120	\/	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current a	T _C =25°C	I_D	52	Α	
Pulsed Drain Current ^b		I _{DM}	200	A	
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	52	Α	
Power Dissipation ^a	T _C =25°C	P_D	40	W	
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W	
Maximum Junction-to-Case	$R_{ heta JC}$	3	C/VV	

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

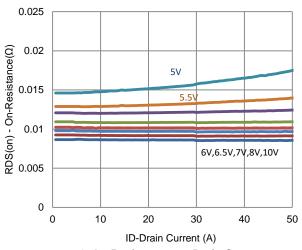
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 96 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zelo Gale Voltage Dialii Cullent	I _{DSS}	$V_{DS} = 96 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α	
Drain Course On Besistance a	r	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$			10	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 6.5 \text{ V}, I_D = 25 \text{ A}$			14		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 30 \text{ A}$		58		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 30 \text{ A}, V_{GS} = 0 \text{ V}$		0.88		V	
Dynamic ^b							
Total Gate Charge	Q_g	$V_{DS} = 60 \text{ V}, V_{GS} = 6.5 \text{ V},$		30			
Gate-Source Charge	Q_gs	$I_{DS} = 30 \text{ V}, V_{GS} = 0.3 \text{ V},$ $I_{D} = 30 \text{ A}$		12		nC	
Gate-Drain Charge	Q_gd	1 ₀ = 33 / C		12			
Turn-On Delay Time	$t_{d(on)}$	V 60 V B = 2.0		17			
Rise Time	t _r	$V_{DS} = 60 \text{ V}, R_{L} = 2 \Omega,$ $I_{D} = 30 \text{ A},$		16		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		47		ns	
Fall Time	t _f	V GEN = 10 V, 1 GEN 0 12		68			
Input Capacitance	C _{iss}			2318			
Output Capacitance	C _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		585		pF	
Reverse Transfer Capacitance	C_{rss}			24			

Notes

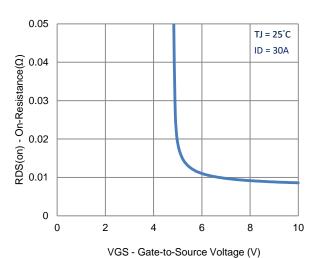
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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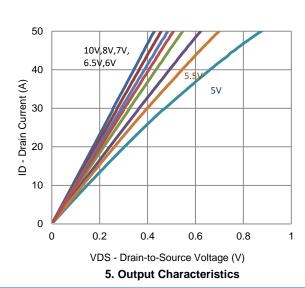
Typical Electrical Characteristics

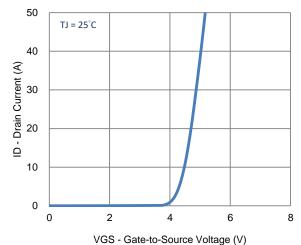


1. On-Resistance vs. Drain Current

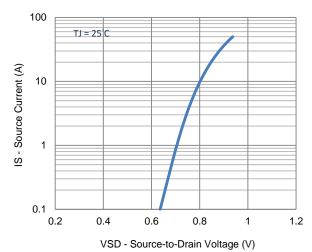


3. On-Resistance vs. Gate-to-Source Voltage

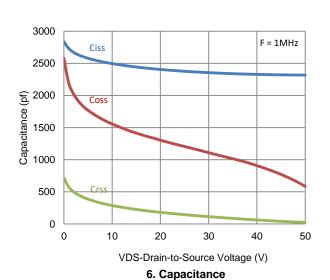




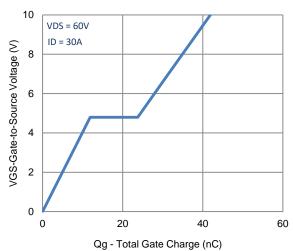
2. Transfer Characteristics

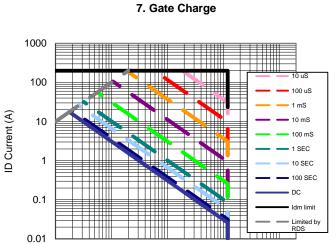


4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics



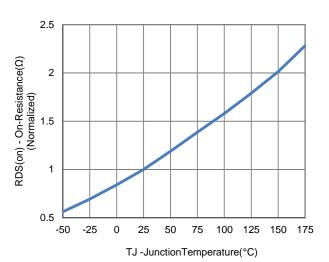


VDS Drain to Source Voltage (V) 9. Safe Operating Area

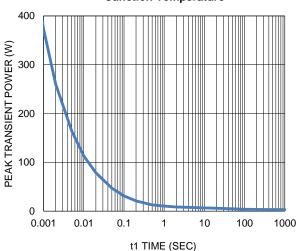
100

1000

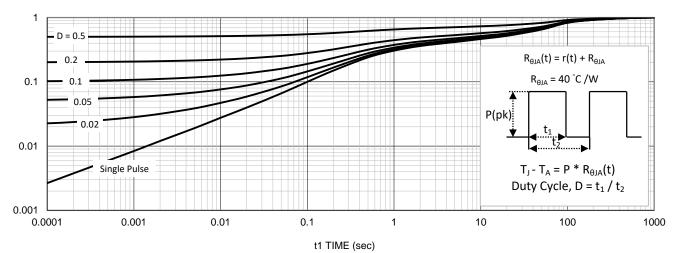
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8. Normalized On-Resistance Vs Junction Temperature



10. Single Pulse Maximum Power Dissipation

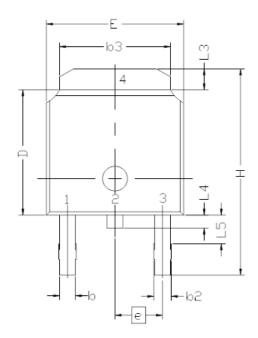


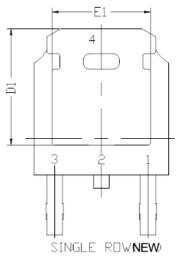
11. Normalized Thermal Transient Junction to Ambient

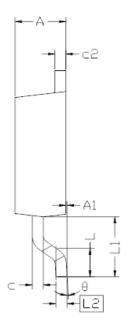
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Package Information







CVMDEI	DIMENS:	[DNAL	REQMTS		
SYMBOL	MIN	NDM	MAX		
E	6.40	6.60	6.731		
L	1.40	1.52	1.77		
L1	2	.743 R	ĖF		
L2	0.	.508 BS			
L3	0.89		1.27		
L4	0.64		1.01		
L5					
D	6.00	6.10	6.223		
Н	9.40	10.00	10.40		
b	0.64	0.76	0.88		
b2	0.77	0.84	1.14		
b3	5.21	5.34	5.46		
е	2.				
Α	2,20	2,30	2.38		
A1	0		0.127		
C	0.45	0.50	0.60		
c2	0.45	0,50	0.58		
D1	5.30				
E1	4.40				
θ	0°		10°		

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.